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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	72MHz
Connectivity	CANbus, I²C, IrDA, LINbus, SPI, UART/USART, USB
Peripherals	DMA, I²S, POR, PWM, WDT
Number of I/O	51
Program Memory Size	512KB (512K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	64K x 8
Voltage - Supply (Vcc/Vdd)	2V ~ 3.6V
Data Converters	A/D 16x12b; D/A 1x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f302ret6tr

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Table 2. STM32F302xD/E family device features and peripheral counts

Peripheral		STM32F302Rx		STM32F302Vx		STM32F302Zx	
Flash (Kbytes)		384	512	384	512	384	512
SRAM (Kbytes) on data bus		64					
FMC (flexible memory controller)		NO		YES			
Timers	Advanced control	1 (16-bit)					
	General purpose	5 (16-bit) 1 (32-bit)					
	Basic	1 (16-bit)					
	PWM channels (all) (1)	26					
	PWM channels (except complementary)	20					
Communication interfaces	SPI (I^2S)(2)	4(2)					
	I^2C	3					
	USART	3					
	UART	2					
	CAN	1					
	USB	1					
GPIOs	Normal I/Os (TC, TTa)	26		37 in WLCSP100,44 in LQFP100 and UFBGA100		45	
	5-volt tolerant I/Os (FT, FTf)	25		42 in LQFP100 40 in WLCSP100 and UFBGA100		70	
DMA channels		12					
Capacitive sensing channels		18		24			
12-bit ADCs		2 16 channels		2 17 channels		2 18 channels	
12-bit DAC channels		1					
Analog comparator		4					
Operational amplifiers		2					
CPU frequency		72 MHz					
Operating voltage		2.0 to 3.6 V					
Operating temperature		Ambient operating temperature: - 40 to 85 °C / - 40 to 105 °C Junction temperature: - 40 to 125 °C					
Packages		LQFP64		LQFP100 ,WLCSP100 UFBGA100		LQFP144	

1. This total number considers also the PWMs generated on the complementary output channels.
2. The SPI interfaces works in an exclusive way in either the SPI mode or the I^2S audio mode.

3.14.1 Temperature sensor

The temperature sensor (TS) generates a voltage V_{SENSE} that varies linearly with temperature.

The temperature sensor is internally connected to the ADC1_IN16 input channel which is used to convert the sensor output voltage into a digital value.

The sensor provides good linearity but it has to be calibrated to obtain good overall accuracy of the temperature measurement. As the offset of the temperature sensor varies from chip to chip due to process variation, the uncalibrated internal temperature sensor is suitable for applications that detect temperature changes only.

To improve the accuracy of the temperature sensor measurement, each device is individually factory-calibrated by ST. The temperature sensor factory calibration data are stored by ST in the system memory area, accessible in read-only mode.

3.14.2 Internal voltage reference (V_{REFINT})

The internal voltage reference (V_{REFINT}) provides a stable (bandgap) voltage output for the ADC and Comparators. V_{REFINT} is internally connected to the ADCx_IN18, x=1...4 input channel. The precise voltage of V_{REFINT} is individually measured for each part by ST during production test and stored in the system memory area. It is accessible in read-only mode.

3.14.3 V_{BAT} battery voltage monitoring

This embedded hardware feature allows the application to measure the V_{BAT} battery voltage using the internal ADC channel ADC1_IN17. As the V_{BAT} voltage may be higher than V_{DDA}, and thus outside the ADC input range, the V_{BAT} pin is internally connected to a bridge divider by 2. As a consequence, the converted digital value is half the V_{BAT} voltage.

3.14.4 OPAMP reference voltage (VREFOPAMP)

Every OPAMP reference voltage can be measured using a corresponding ADC internal channel: VREFO, VREFOPAMP1 connected to ADC1 channel 15, VREFOPAMP2 connected to ADC2 channel 17.

3.15 Digital-to-analog converter (DAC)

One 12-bit buffered DAC channel can be used to convert digital signals into analog voltage signal outputs. The chosen design structure is composed of integrated resistor strings and an amplifier in inverting configuration.

This digital interface supports the following features:

- One DAC output channel
- 8-bit or 10-bit monotonic output
- Left or right data alignment in 12-bit mode
- Synchronized update capability
- Noise-wave generation
- Triangular-wave generation
- DMA capability (for each channel)

Table 5. Timer feature comparison (continued)

Timer type	Timer	Counter resolution	Counter type	Prescaler factor	DMA request generation	Capture/ compare channels	Complementary outputs
General-purpose	TIM3, TIM4	16-bit	Up, Down, Up/Down	Any integer between 1 and 65536	Yes	4	No
General-purpose	TIM15	16-bit	Up	Any integer between 1 and 65536	Yes	2	1
General-purpose	TIM16, TIM17	16-bit	Up	Any integer between 1 and 65536	Yes	1	1
Basic	TIM6	16-bit	Up	Any integer between 1 and 65536	Yes	0	No

Note: TIM1/2/3/4/15/16/17 can have PLL as clock source, and therefore can be clocked at 144 MHz.

3.18.1 Advanced timers (TIM1)

The advanced-control timer (TIM1) can be seen as a three-phase PWM multiplexed on six channels. It has complementary PWM outputs with programmable inserted dead-times. It can also be seen as a complete general-purpose timer. The four independent channels can be used for:

- Input capture
- Output compare
- PWM generation (edge or center-aligned modes) with full modulation capability (0-100%)
- One-pulse mode output

In debug mode, the advanced-control timer counter can be frozen and the PWM outputs disabled to turn off any power switches driven by these outputs.

Many features are shared with those of the general-purpose TIM timer (described in *Section 3.18.2*) using the same architecture, so the advanced-control timers can work together with the TIM timers via the Timer Link feature for synchronization or event chaining.

3.18.2 General-purpose timers (TIM2, TIM3, TIM4, TIM15, TIM16, TIM17)

There are up to six synchronizable general-purpose timers embedded in the STM32F302xD/E (see *Table 5* for differences). Each general-purpose timer can be used to generate PWM outputs, or act as a simple time base.

Table 14. STM32F302xD/E alternate function mapping (continued)

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11	AF12	AF13	AF14	AF15
		SYS_AF	TIM2/15/16/17/EVENT	I2C3/TIM12/3/4/8/20/15/GPCOMP1	I2C3//15/TSC	I2C1/2/TIM1/8/16/17	SPI1/SPI2/I2S2/SPI3/I2S3/SPI4/UART4/5/Infrared	SPI2/I2S2/SPI3/I2S3/TIM1/8/20/Infrared	USART1/2/3/CAN/GPCOMP6	I2C3/GPCOMP1/2/3/4/5/6	CAN/TIM1/8/15	TIM2/3/4/8/17	TIM1/8	FSMC/TIM1	-	-	EVENT
Port D	PD5	-	EVENT OUT	-	-	-	-	-	USART2_TX	-	-	-	-	FMC_NWE	-	-	-
	PD6	-	EVENT OUT	TIM2_CH4	-	-	-	-	USART2_RX	-	-	-	-	FMC_NWAIT	-	-	-
	PD7	-	EVENT OUT	TIM2_CH3	-	-	-	-	USART2_CK	-	-	-	-	FMC_NE1/FMC_NCE2	-	-	-
	PD8	-	EVENT OUT	-	-	-	-	-	USART3_TX	-	-	-	-	FMC_D13	-	-	-
	PD9	-	EVENT OUT	-	-	-	-	-	USART3_RX	-	-	-	-	FMC_D14	-	-	-
	PD10	-	EVENT OUT	-	-	-	-	-	USART3_CK	-	-	-	-	FMC_D15	-	-	-
	PD11	-	EVENT OUT	-	-	-	-	-	USART3_CTS	-	-	-	-	FMC_A16	-	-	-
	PD12	-	EVENT OUT	TIM4_CH1	TSC_G8_IO1	-	-	-	USART3_RTS	-	-	-	-	FMC_A17	-	-	-
	PD13	-	EVENT OUT	TIM4_CH2	TSC_G8_IO2	-	-	-	-	-	-	-	-	FMC_A18	-	-	-
	PD14	-	EVENT OUT	TIM4_CH3	TSC_G8_IO3	-	-	-	-	-	-	-	-	FMC_D0	-	-	-
	PD15	-	EVENT OUT	TIM4_CH4	TSC_G8_IO4	-	-	SPI2_NSS	-	-	-	-	-	FMC_D1	-	-	-

Table 14. STM32F302xD/E alternate function mapping (continued)

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11	AF12	AF13	AF14	AF15
		SYS_AF	TIM2/15/16/17/EVENT	I2C3/TIM1/2/3/4/8/20/15/GPCOMP1	I2C3//15/TSC	I2C1/2/TIM1/8/16/17	SPI1/SPI2/I2S2/SPI3/I2S3/SPI4/UART4/5/Infrared	SPI2/I2S2/SPI3/I2S3/TIM1/8/20/Infrared	USART1/2/3/CAN/GPCOMP6	I2C3/GPCOMP1/2/3/4/5/6	CAN/TIM1/8/15	TIM2/3/4/8/17	TIM1/8	FSMC/TIM1	-	-	EVENT
Port G	PG5	-	EVENT OUT	-	-	-	-	-	-	-	-	-	-	FMC_A15	-	-	-
	PG6	-	EVENT OUT	-	-	-	-	-	-	-	-	-	-	FMC_INT2	-	-	-
	PG7	-	EVENT OUT	-	-	-	-	-	-	-	-	-	-	FMC_INT3	-	-	-
	PG8	-	EVENT OUT	-	-	-	-	-	-	-	-	-	-	-	-	-	-
	PG9	-	EVENT OUT	-	-	-	-	-	-	-	-	-	-	FMC_NE2/FMC_NCE3	-	-	-
	PG10	-	EVENT OUT	-	-	-	-	-	-	-	-	-	-	FMC_NCE4_1/FMC_NE3	-	-	-
	PG11	-	EVENT OUT	-	-	-	-	-	-	-	-	-	-	FMC_NCE4_2	-	-	-
	PG12	-	EVENT OUT	-	-	-	-	-	-	-	-	-	-	FMC_NE4	-	-	-
	PG13	-	EVENT OUT	-	-	-	-	-	-	-	-	-	-	FMC_A24	-	-	-
	PG14	-	EVENT OUT	-	-	-	-	-	-	-	-	-	-	FMC_A25	-	-	-
	PG15	-	EVENT OUT	-	-	-	-	-	-	-	-	-	-	-	-	-	-

6 Electrical characteristics

6.1 Parameter conditions

Unless otherwise specified, all voltages are referenced to V_{SS}.

6.1.1 Minimum and maximum values

Unless otherwise specified, the minimum and maximum values are guaranteed in the worst conditions of ambient temperature, supply voltage and frequencies by tests in production on 100% of the devices with an ambient temperature at T_A = 25 °C and T_A = $T_A$max (given by the selected temperature range).

Data based on characterization results, design simulation and/or technology characteristics are indicated in the table footnotes and are not tested in production. Based on characterization, the minimum and maximum values refer to sample tests and represent the mean value plus or minus three times the standard deviation (mean±3σ).

6.1.2 Typical values

Unless otherwise specified, typical data are based on T_A = 25 °C, V_{DD} = V_{DDA} = 2.0 to 3.6 V. They are given only as design guidelines and are not tested.

Typical ADC accuracy values are determined by characterization of a batch of samples from a standard diffusion lot over the full temperature range, where 95% of the devices have an error less than or equal to the value indicated (mean±2σ).

6.1.3 Typical curves

Unless otherwise specified, all typical curves are given only as design guidelines and are not tested.

6.1.4 Loading capacitor

The loading conditions used for pin parameter measurement are shown in *Figure 10*.

6.1.5 Pin input voltage

The input voltage measurement on a pin of the device is described in *Figure 11*.

Figure 10. Pin loading conditions

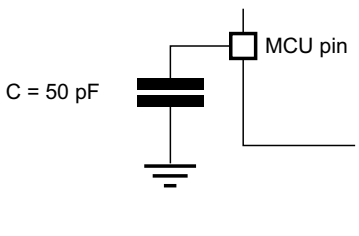
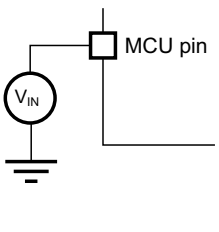


Figure 11. Pin input voltage



All Run-mode current consumption measurements given in this section are performed with a reduced code that gives a consumption equivalent to CoreMark code.

Note: The total current consumption is the sum of I_{DD} and I_{DDA}.

Typical and maximum current consumption

The MCU is placed under the following conditions:

- All I/O pins are in input mode with a static value at V_{DD} or V_{SS} (no load)
- All peripherals are disabled except when explicitly mentioned
- The Flash memory access time is adjusted to the f_{HCLK} frequency (0 wait state from 0 to 24 MHz,1 wait state from 24 to 48 MHz and 2 wait states from 48 to 72 MHz)
- Prefetch in ON (reminder: this bit must be set before clock setting and bus prescaling)
- When the peripherals are enabled $f_{PCLK2} = f_{HCLK}$ and $f_{PCLK1} = f_{HCLK/2}$
- When f_{HCLK} > 8 MHz, the PLL is ON and the PLL input is equal to HSI/2 (4 MHz) or HSE (8 MHz) in bypass mode.

The parameters given in *Table 25* to *Table 29* are derived from tests performed under ambient temperature and supply voltage conditions summarized in *Table 19*.

Table 25. Typical and maximum current consumption from V_{DD} supply at V_{DD} = 3.6V

Symbol	Parameter	Conditions	f_{HCLK}	All peripherals enabled				All peripherals disabled				Unit
				Typ	Max @ T_A(1)			Typ	Max @ T_A(1)			
					25 °C	85 °C	105 °C		25 °C	85 °C	105 °C	
I_{DD}	Supply current in Run mode, executing from Flash	External clock (HSE bypass)	72 MHz	66.4	76.5	76.9	77.4	33.0	37.2	38.1	38.9	mA
			64 MHz	59.8	66.4	67.7	68.6	29.7	33.5	34.3	35.0	
			48 MHz	47.3	53.7	53.8	55.1	23.2	26.2	27.1	28.0	
			32 MHz	33.3	36.8	37.4	38.5	16.8	19.8	20.6	21.4	
			24 MHz	26.0	29.4	30.0	31.2	13.5	16.6	17.4	18.6	
			8 MHz	10.7	13.8	14.4	15.3	6.63	10.2	10.5	11.2	
			1 MHz	4.27	7.47	8.13	8.90	3.78	7.40	7.70	8.50	
		Internal clock (HSI)	64 MHz	55.6	59.6	62.8	63.2	29.4	33.1	34.5	35.0	
			48 MHz	43.6	47.0	49.2	50.1	23.1	26.2	27.1	28.0	
			32 MHz	30.8	33.6	35.3	35.8	16.7	19.8	20.6	21.5	
			24 MHz	24.0	28.0	28.2	29.7	13.5	16.5	17.5	18.4	
			8 MHz	10.5	13.6	14.7	15.2	6.63	9.74	10.6	11.2	
I_{DD}	Supply current in Run mode, executing from RAM	External clock (HSE bypass)	72 MHz	66.2	76.2(2)	76.7	77.2(2)	32.8	36.9(2)	37.7	38.5(2)	
			64 MHz	59.6	66.2	67.6	68.4	29.3	33.1	33.9	34.4	
			48 MHz	47.0	53.4	53.6	54.9	22.4	25.6	26.2	27.2	
			32 MHz	33.0	36.6	37.2	38.1	16.0	19.0	19.5	20.4	
			24 MHz	25.6	29.0	29.5	30.6	12.8	15.7	16.3	17.6	
			8 MHz	10.3	13.4	13.8	14.7	6.40	9.48	9.93	10.90	

I/O system current consumption

The current consumption of the I/O system has two components: static and dynamic.

I/O static current consumption

All the I/Os used as inputs with pull-up generate current consumption when the pin is externally held low. The value of this current consumption can be simply computed by using the pull-up/pull-down resistors values given in *Table 66: I/O static characteristics*.

For the output pins, any external pull-down or external load must also be considered to estimate the current consumption.

Additional I/O current consumption is due to I/Os configured as inputs if an intermediate voltage level is externally applied. This current consumption is caused by the input Schmitt trigger circuits used to discriminate the input value. Unless this specific configuration is required by the application, this supply current consumption can be avoided by configuring these I/Os in analog mode. This is notably the case of ADC input pins which should be configured as analog inputs.

Caution: Any floating input pin can also settle to an intermediate voltage level or switch inadvertently, as a result of external electromagnetic noise. To avoid current consumption related to floating pins, they must either be configured in analog mode, or forced internally to a definite digital value. This can be done either by using pull-up/down resistors or by configuring the pins in output mode.

I/O dynamic current consumption

In addition to the internal peripheral current consumption (see *Table 33: Peripheral current consumption*), the I/Os used by an application also contribute to the current consumption. When an I/O pin switches, it uses the current from the MCU supply voltage to supply the I/O pin circuitry and to charge/discharge the capacitive load (internal or external) connected to the pin:

$$I_{SW} = V_{DD} \times f_{SW} \times C$$

where:

I_{SW} is the current sunk by a switching I/O to charge/discharge the capacitive load

V_{DD} is the MCU supply voltage

f_{SW} is the I/O switching frequency

C is the total capacitance seen by the I/O pin: $C = C_{INT} + C_{EXT} + C_S$

The test pin is configured in push-pull output mode and is toggled by software at a fixed frequency.

On-chip peripheral current consumption

The MCU is placed under the following conditions:

- all I/O pins are in analog input configuration
- all peripherals are disabled unless otherwise mentioned
- the given value is calculated by measuring the current consumption
  - with all peripherals clocked off
  - with only one peripheral clocked on
- ambient operating temperature at 25°C and $V_{DD} = V_{DDA} = 3.3$ V.

Table 33. Peripheral current consumption

Peripheral	Typical consumption(1)	Unit
	I_{DD}	
BusMatrix (2)	8.3	µA/MHz
DMA1	7.0	
DMA2	5.4	
FSMC	35.0	
CRC	1.5	
GPIOH	1.3	
GPIOA	5.4	
GPIOB	5.3	
GPIOC	5.4	
GPIOD	5.0	
GPIOE	5.4	
GPIOF	5.2	
GPIOG	5.0	
TSC	5.2	
ADC1&2	15.4	
APB2-Bridge (3)	3.1	
SYSCFG	4.0	
TIM1	26.0	
USART1	17.7	
SPI4	6.2	
TIM15	11.9	
TIM16	8.0	
TIM17	8.5	

6.3.10 Memory characteristics

Flash memory

The characteristics are given at T_A = –40 to 105 °C unless otherwise specified.

Table 43. Flash memory characteristics

Symbol	Parameter	Conditions	Min	Typ	Max(1)	Unit
t_{prog}	16-bit programming time	T_A = –40 to +105 °C	40	53.5	60	µs
t_{ERASE}	Page (2 KB) erase time	T_A = –40 to +105 °C	20	-	40	ms
t_{ME}	Mass erase time	T_A = –40 to +105 °C	20	-	40	ms
I_{DD}	Supply current	Write mode	-	-	10	mA
		Erase mode	-	-	12	mA

1. Guaranteed by design, not tested in production.

Table 44. Flash memory endurance and data retention

Symbol	Parameter	Conditions	Value	Unit
			Min(1)	
N_{END}	Endurance	T_A = –40 to +85 °C (6 suffix versions) T_A = –40 to +105 °C (7 suffix versions)	10	kcycles
t_{RET}	Data retention	1 kcycle(2) at T_A = 85 °C	30	Years
		1 kcycle(2) at T_A = 105 °C	10	
		10 kcycle(2) at T_A = 55 °C	20	

1. Data based on characterization results, not tested in production.
2. Cycling performed over the whole temperature range.

6.3.11 FSMC characteristics

Unless otherwise specified, the parameters given in *Table 45* to *Table 60* for the FSMC interface are derived from tests performed under the ambient temperature, f_{HCLK} frequency and V_{DD} supply voltage conditions summarized in *Table 19* with the following configuration:

- Output speed is set to OSPEEDRy[1:0] = 11
- Capacitive load C = 30 pF
- Measurement points are done at CMOS levels: 0.5VDD

Refer to *Section 6.3.15: I/O port characteristics*: for more details on the input/output characteristics.

Table 50. Asynchronous multiplexed PSRAM/NOR read timings(1) (continued)

Symbol	Parameter	Min	Max	Unit
$t_{v(BL\_NE)}$	FMC_NEx low to FMC_BL valid	-	2	ns
$t_{su(Data\_NE)}$	Data to FMC_NEx high setup time	THCLK	-	
$t_{su(Data\_NOE)}$	Data to FMC_NOE high setup time	THCLK+1	-	
$t_{h(Data\_NE)}$	Data hold time after FMC_NEx high	0	-	
$t_{h(Data\_NOE)}$	Data hold time after FMC_NOE high	0	-	

1. Based on characterization, not tested in production.

Figure 23. Asynchronous multiplexed PSRAM/NOR write timings

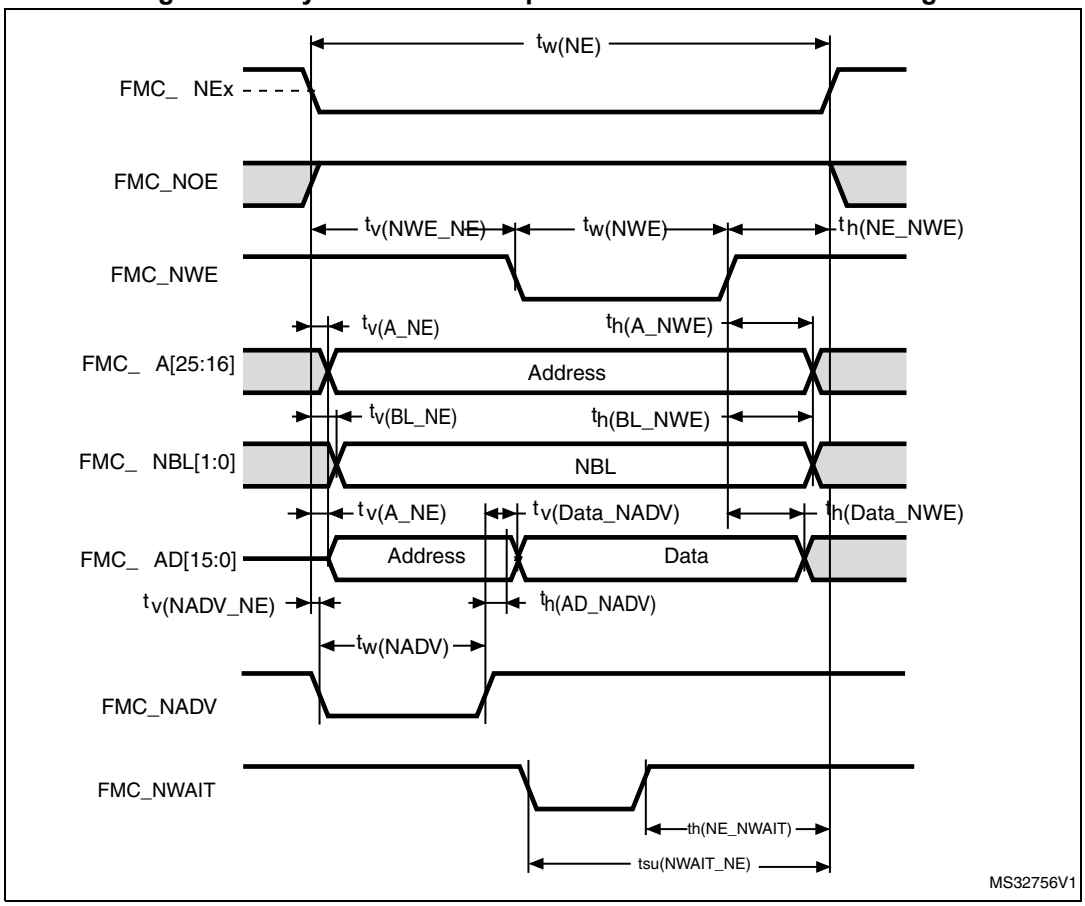


Table 51. Asynchronous multiplexed PSRAM/NOR write timings(1)

Symbol	Parameter	Min	Max	Unit
$t_{w(NE)}$	FMC_NE low time	4THCLK-1	4THCLK+1	ns
$t_{v(NWE\_NE)}$	FMC_NEx low to FMC_NWE low	THCLK	THCLK+0.5	
$t_{w(NWE)}$	FMC_NWE low time	2THCLK-0.5	2THCLK+1	
$t_{h(NE\_NWE)}$	FMC_NWE high to FMC_NE high hold time	THCLK-0.5	-	
$t_{v(A\_NE)}$	FMC_NEx low to FMC_A valid	-	5	
$t_{v(NADV\_NE)}$	FMC_NEx low to FMC_NADV low	1	2.5	
$t_{w(NADV)}$	FMC_NADV low time	THCLK-2	THCLK+2	
$t_{h(AD\_NADV)}$	FMC_AD(adress) valid hold time after FMC_NADV high)	THCLK-2	-	
$t_{h(A\_NWE)}$	Address hold time after FMC_NWE high	THCLK-1	-	
$t_{h(BL\_NWE)}$	FMC_BL hold time after FMC_NWE high	THCLK-0.5	-	
$t_{v(BL\_NE)}$	FMC_NEx low to FMC_BL valid	-	1	
$t_{v(Data\_NADV)}$	FMC_NADV high to Data valid	-	THCLK +3.5	
$t_{h(Data\_NWE)}$	Data hold time after FMC_NWE high	THCLK +0.5	-	

1. Based on characterization, not tested in production.

Table 52. Asynchronous multiplexed PSRAM/NOR write-NWAIT timings(1)

Symbol	Parameter	Min	Max	Unit
$t_{w(NE)}$	FMC_NE low time	9THCLK	9THCLK+0.5	ns
$t_{w(NWE)}$	FMC_NWE low time	6THCLK	6THCLK+2	
$t_{su(NWAIT\_NE)}$	FMC_NWAIT valid before FMC_NEx high	5THCLK+6	-	
$t_{h(NE\_NWAIT)}$	FMC_NEx hold time after FMC_NWAIT invalid	5THCLK-5	-	

1. Based on characterization, not tested in production.

Synchronous waveforms and timings

Figure 24 and *Figure 27* present the synchronous waveforms and *Table 53* to *Table 56* provide the corresponding timings. The results shown in these tables are obtained with the following FSMC configuration:

- BurstAccessMode = FMC_BurstAccessMode_Enable;
- MemoryType = FMC_MemoryType_CRAM;
- WriteBurst = FMC_WriteBurst_Enable;
- CLKDivision = 1;
- DataLatency = 2 for NOR Flash; DataLatency = 0 for PSRAM

In all timing tables, the THCLK is the HCLK clock period (with maximum FMC_CLK = 36 MHz).

Figure 37. TC and TTa I/O input characteristics - TTL port

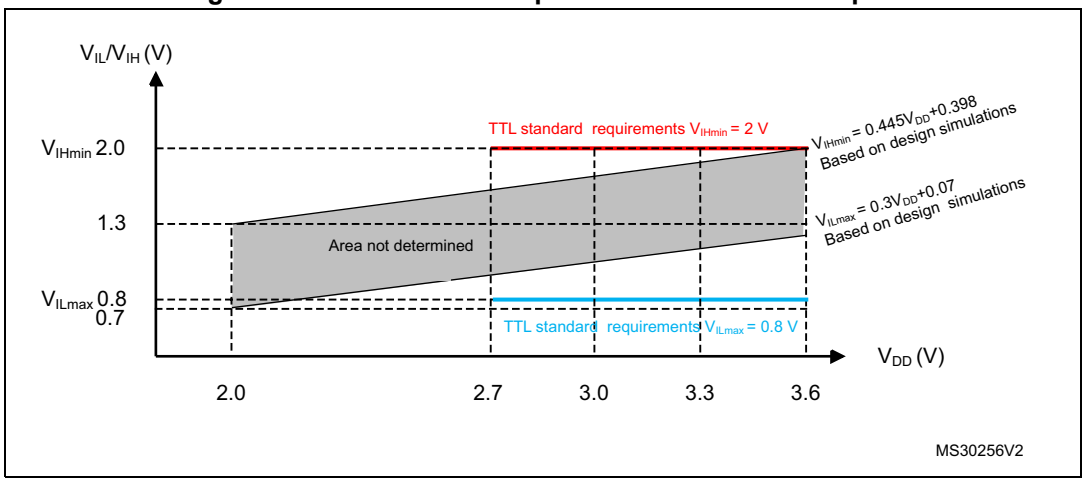


Figure 38. Five volt tolerant (FT and FTf) I/O input characteristics - CMOS port

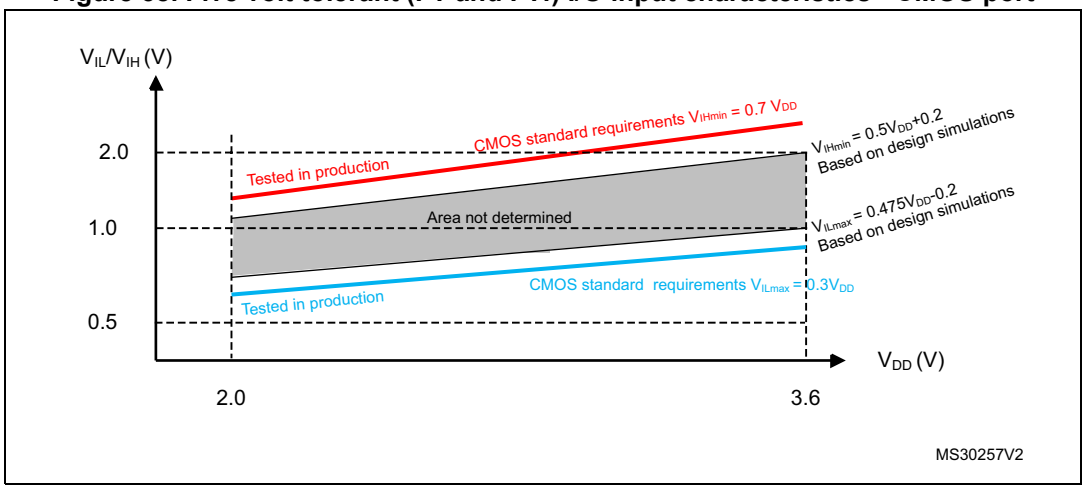


Figure 39. Five volt tolerant (FT and FTf) I/O input characteristics - TTL port

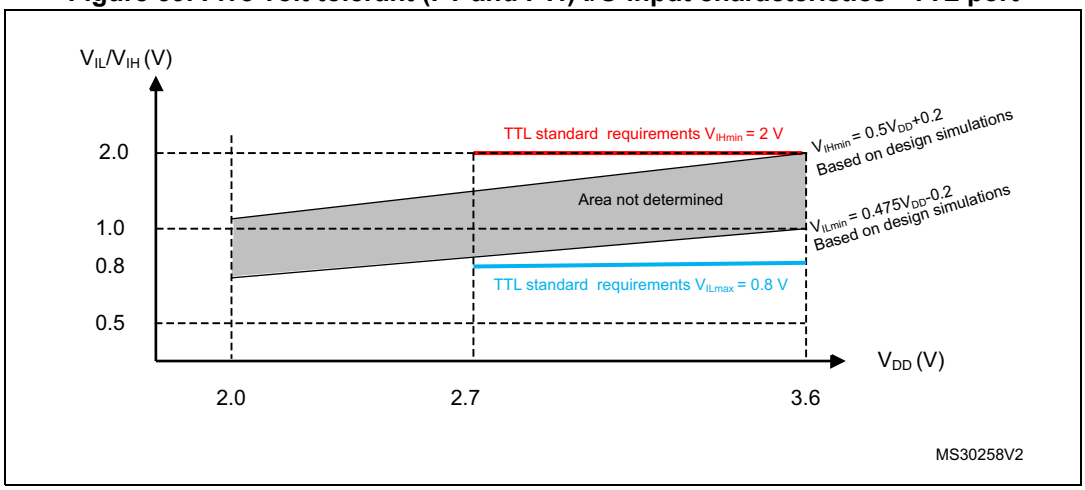


Table 71. IWDG min/max timeout period at 40 kHz (LSI) (1)

Prescaler divider	PR[2:0] bits	Min timeout (ms) RL[11:0]= 0x000	Max timeout (ms) RL[11:0]= 0xFFF
/4	0	0.1	409.6
/8	1	0.2	819.2
/16	2	0.4	1638.4
/32	3	0.8	3276.8
/64	4	1.6	6553.6
/128	5	3.2	13107.2
/256	7	6.4	26214.4

1. These timings are given for a 40 kHz clock but the microcontroller internal RC frequency can vary from 30 to 60 kHz. Moreover, given an exact RC oscillator frequency, the exact timings still depend on the phasing of the APB interface clock versus the LSI clock so that there is always a full RC period of uncertainty.

Table 72. WWDG min-max timeout value @72 MHz (PCLK)(1)

Prescaler	WDGTB	Min timeout value	Max timeout value
1	0	0.05687	3.6409
2	1	0.1137	7.2817
4	2	0.2275	14.564
8	3	0.4551	29.127

1. Guaranteed by design, not tested in production.

6.3.18 Communications interfaces

I²C interface characteristics

The I²C interface meets the timings requirements of the I²C-bus specification and user manual rev.03 for:

- Standard-mode (Sm): with a bit rate up to 100 kbit/s
- Fast-mode (Fm): with a bit rate up to 400 kbit/s
- Fast-mode Plus (Fm+): with a bit rate up to 1Mbits/s

The I²C timings requirements are guaranteed by design when the I²C peripheral is properly configured (refer to Reference manual).

The SDA and SCL I/O requirements are met with the following restrictions: the SDA and SCL I/O pins are “true” open-drain. When configured as open-drain, the PMOS connected between the I/O pin and VDDIOx is disabled, but is still present. Only FTf I/O pins support Fm+ low level output current maximum requirement. Refer to *Section 6.3.15: I/O port characteristics*.

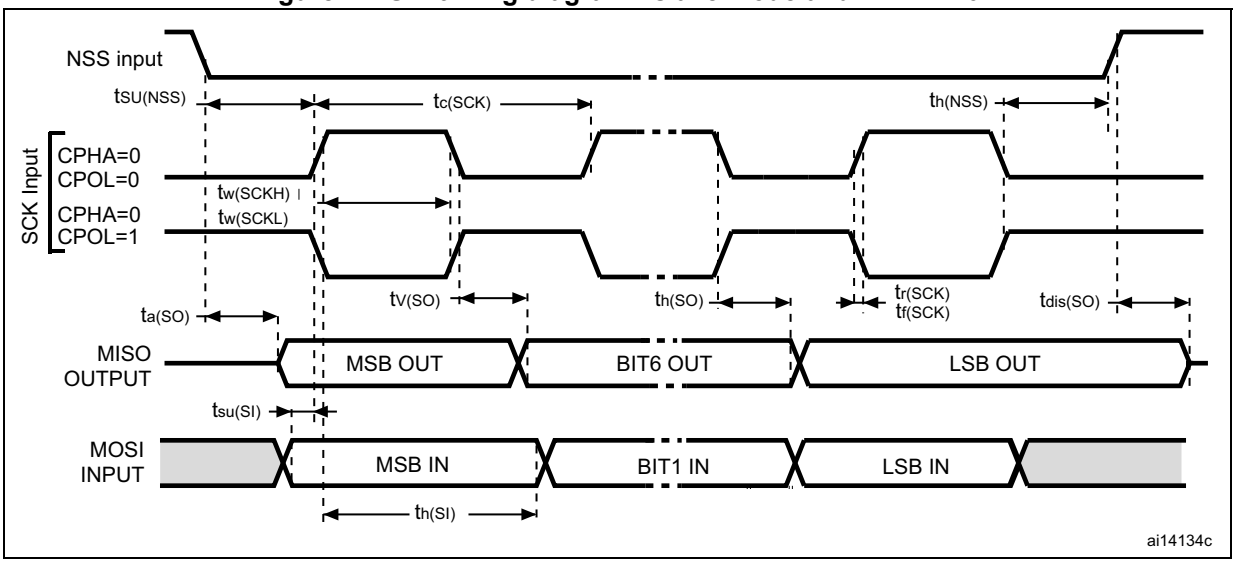
All I²C I/Os embed an analog filter, refer to the *Table 73: I2C analog filter characteristics*.

Table 74. SPI characteristics(1) (continued)

Symbol	Parameter	Conditions	Min	Typ.	Max	Unit
$t_{v(SO)}$	Data output valid time	Slave mode 2.7 V<V_{DD}<3.6 V	-	15	22	
		Slave mode 2 V<V_{DD}<3.6 V	-	15	30	
$t_{v(MO)}$		Master mode	-	2	4.5	
$t_{h(SO)}$	Data output hold time	Slave mode	9	-	-	
$t_{h(MO)}$		Master mode	0	-	-	

1. Data based on characterization results, not tested in production.
2. The maximum frequency in Slave transmitter mode is determined by the sum of tv(SO) and tsu(MI) which has to fit into SCK low or high phase preceding the SCK sampling edge. This value can be achieved when the SPI communicates with a master having tsu(MI) = 0 while $Duty_{(SCK)}$ = 50%.

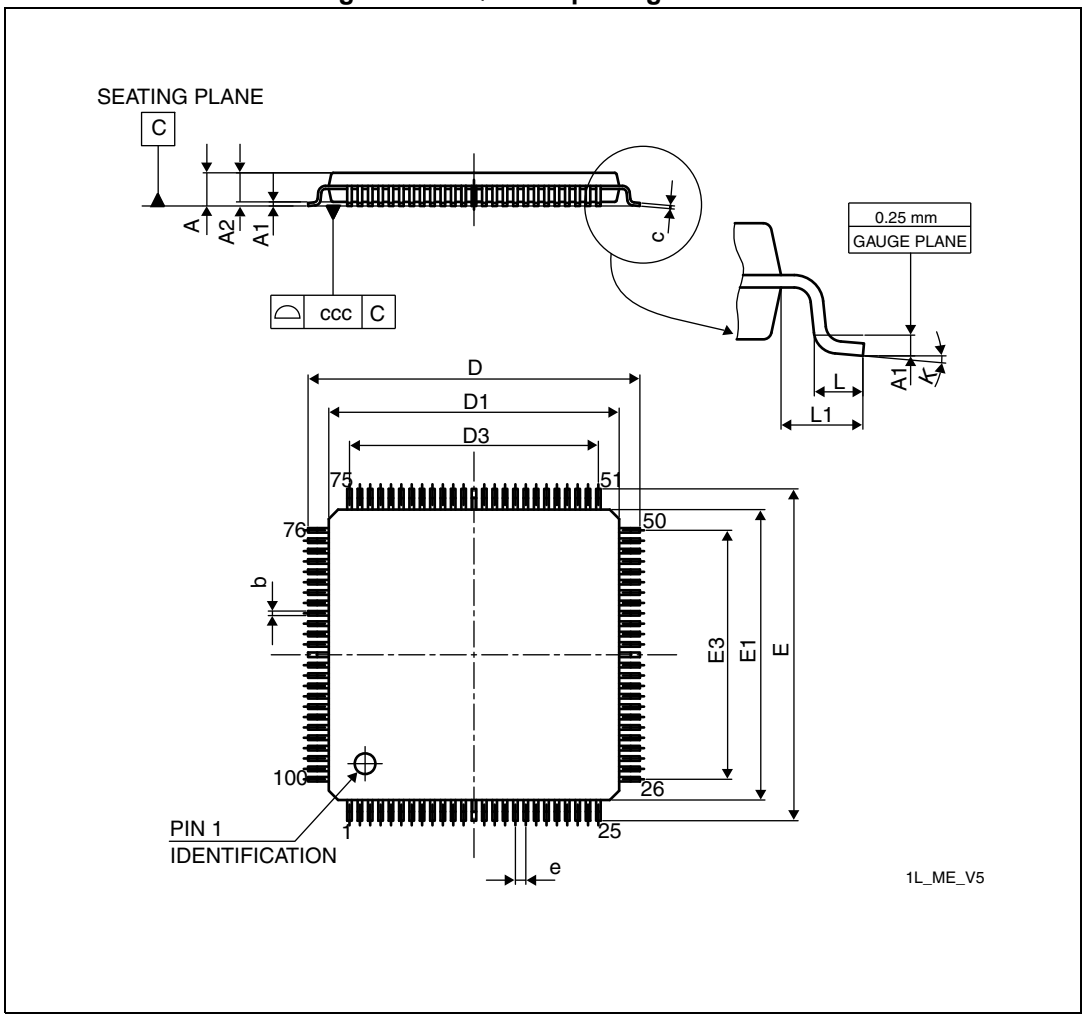
Figure 42. SPI timing diagram - slave mode and CPHA = 0



7.4 LQFP100 package information

LQFP100 is a 100-pin, 14 x 14 mm low-profile quad flat package.

Figure 60. LQFP100 package outline



1. Drawing is not to scale.

Table 95. LQPF100 package mechanical data

Symbol	millimeters			inches[1]		
	Min	Typ	Max	Min	Typ	Max
A	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
c	0.090	-	0.200	0.0035	-	0.0079
D	15.800	16.000	16.200	0.6220	0.6299	0.6378

7.7 Thermal characteristics

The maximum chip junction temperature ($T_J$max) must never exceed the values given in *Table 19: General operating conditions*.

The maximum chip-junction temperature, T_J max, in degrees Celsius, may be calculated using the following equation:

$$T_J \text{ max} = T_A \text{ max} + (P_D \text{ max} \times \Theta_{JA})$$

Where:

- T_A max is the maximum temperature in °C,
- Θ_{JA} is the package junction-to- thermal resistance, in °C/W,
- P_D max is the sum of P_{INT} max and $P_{I/O}$ max (P_D max = P_{INT} max + $P_{I/O}$max),
- P_{INT} max is the product of I_{DD} and V_{DD}, expressed in Watts. This is the maximum chip internal power.

$P_{I/O}$ max represents the maximum power dissipation on output pins where:

$$P_{I/O} \text{ max} = \Sigma (V_{OL} \times I_{OL}) + \Sigma ((V_{DD} - V_{OH}) \times I_{OH}),$$

taking into account the actual V_{OL} / I_{OL} and V_{OH} / I_{OH} of the I/Os at low and high level in the application.

Table 99. Package thermal characteristics

Symbol	Parameter	Value	Unit
Θ_{JA}	**Thermal resistance junction-** LQFP144 - 20 × 20 mm	33	°C/W
	Thermal resistance junction- UFBGA100 - 7 × 7 mm	59	
	Thermal resistance junction- LQFP100 - 14 × 14 mm	42	
	Thermal resistance junction- WLCSP100 - 0.4 mm pitch	44	
	Thermal resistance junction- LQFP64 - 10 × 10 mm / 0.5 mm pitch	46	

7.7.1 Reference document

JESD51-2 Integrated Circuits Thermal Test Method Environment Conditions - Natural Convection (Still Air). Available from www.jedec.org

7.7.2 Selecting the product temperature range

When ordering the microcontroller, the temperature range is specified in the ordering information scheme shown in *Section 8: Part numbering*.

Each temperature range suffix corresponds to a specific guaranteed temperature at maximum dissipation and to a specific maximum junction temperature.

As applications do not commonly use the STM32F302xD/E at maximum dissipation, it is useful to calculate the exact power consumption and junction temperature to determine which temperature range is best suited to the application.

8 Part numbering

For a list of available options (memory, package, and so on) or for further information on any aspect of this device, contact the nearest ST sales office.

Table 100. Ordering information scheme

Example: STM32 F 302 V E T 6 x

Device family

STM32 = ARM-based 32-bit microcontroller

Product type

F = General-purpose

Sub-family

302 = STM32F302xx

Pin count

R = 64 pins

V = 100 pins

Z = 144 pins

Code size

D = 384 Kbytes of Flash memory

E = 512 Kbytes of Flash memory

Package

H = UFBGA

T = LQFP

Y = WLCSP

Temperature range

6 = –40 to 85 °C

7 = –40 to 105 °C

Options

xxx = programmed parts

TR = tape and reel